

(12) **United States Patent**  
**Tan et al.**

(10) **Patent No.:** **US 9,318,399 B2**  
(45) **Date of Patent:** **Apr. 19, 2016**

(54) **SEMICONDUCTOR WAFERS EMPLOYING A  
FIXED-COORDINATE METROLOGY  
SCHEME AND METHODS FOR  
FABRICATING INTEGRATED CIRCUITS  
USING THE SAME**

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(\*) Notice: Subject to any disclaimer, the term of this  
patent is extended or adjusted under 35  
U.S.C. 154(b) by 224 days.

(21) Appl. No.: **14/134,328**

(22) Filed: **Dec. 19, 2013**

(65) **Prior Publication Data**  
US 2015/0179535 A1 Jun. 25, 2015

(51) **Int. Cl.**  
**H01L 23/544** (2006.01)  
**H01L 21/66** (2006.01)  
**G06F 17/50** (2006.01)

(52) **U.S. Cl.**  
CPC ..... **H01L 22/34** (2013.01); **G06F 17/5072**  
(2013.01); **H01L 23/544** (2013.01); **H01L**  
**22/30** (2013.01); **H01L 2223/5446** (2013.01);  
**H01L 2223/54426** (2013.01); **H01L 2924/0002**  
(2013.01)

(58) **Field of Classification Search**  
CPC ..... **H01L 22/34**  
USPC ..... **257/48**  
See application file for complete search history.

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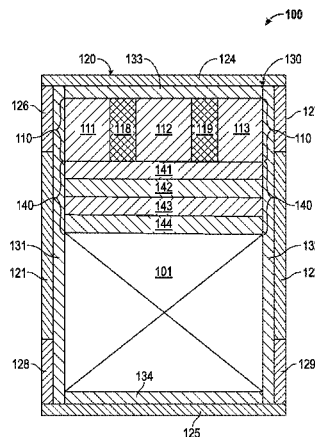
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(57) **ABSTRACT**

Semiconductor wafers employing a fixed coordinate metrology scheme and methods for fabricating integrated circuits using the same are disclosed. In an exemplary embodiment, a semiconductor wafer employing a fixed-coordinate metrology scheme includes an external scribe region in the form of a first rectangular ring, the first rectangular ring defining a first interior space inward from the external scribe region and an interior scribe region in the form of a second rectangular ring, disposed within the first interior space and immediately adjacent to the external scribe region at all points along its exterior perimeter, the second rectangular ring defining a second interior space inward from the interior scribe region, the second interior space being wholly within the first interior space. The semiconductor wafer further includes a technology-specific tile region disposed within the second interior space and immediately adjacent to the interior scribe region and an electrical testable scribe line measurement (ETSML) region disposed within the second interior space and immediately adjacent to both the technology-specific tile region and the interior scribe region. Still further, the semiconductor wafer includes a free floorplan area disposed within the second interior space and immediately adjacent to both the ETSML region and the interior scribe region.

**17 Claims, 6 Drawing Sheets**



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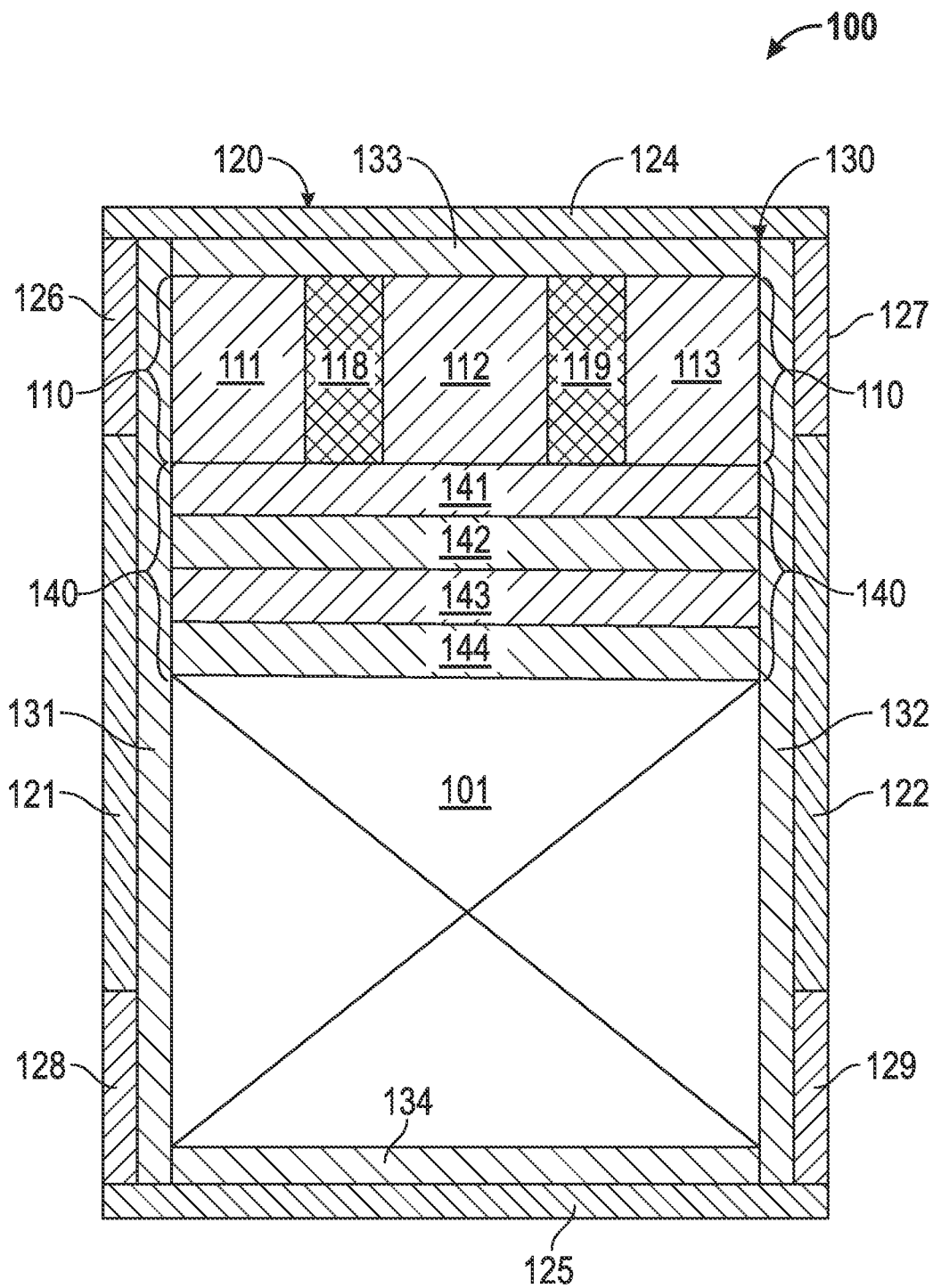


FIG. 1

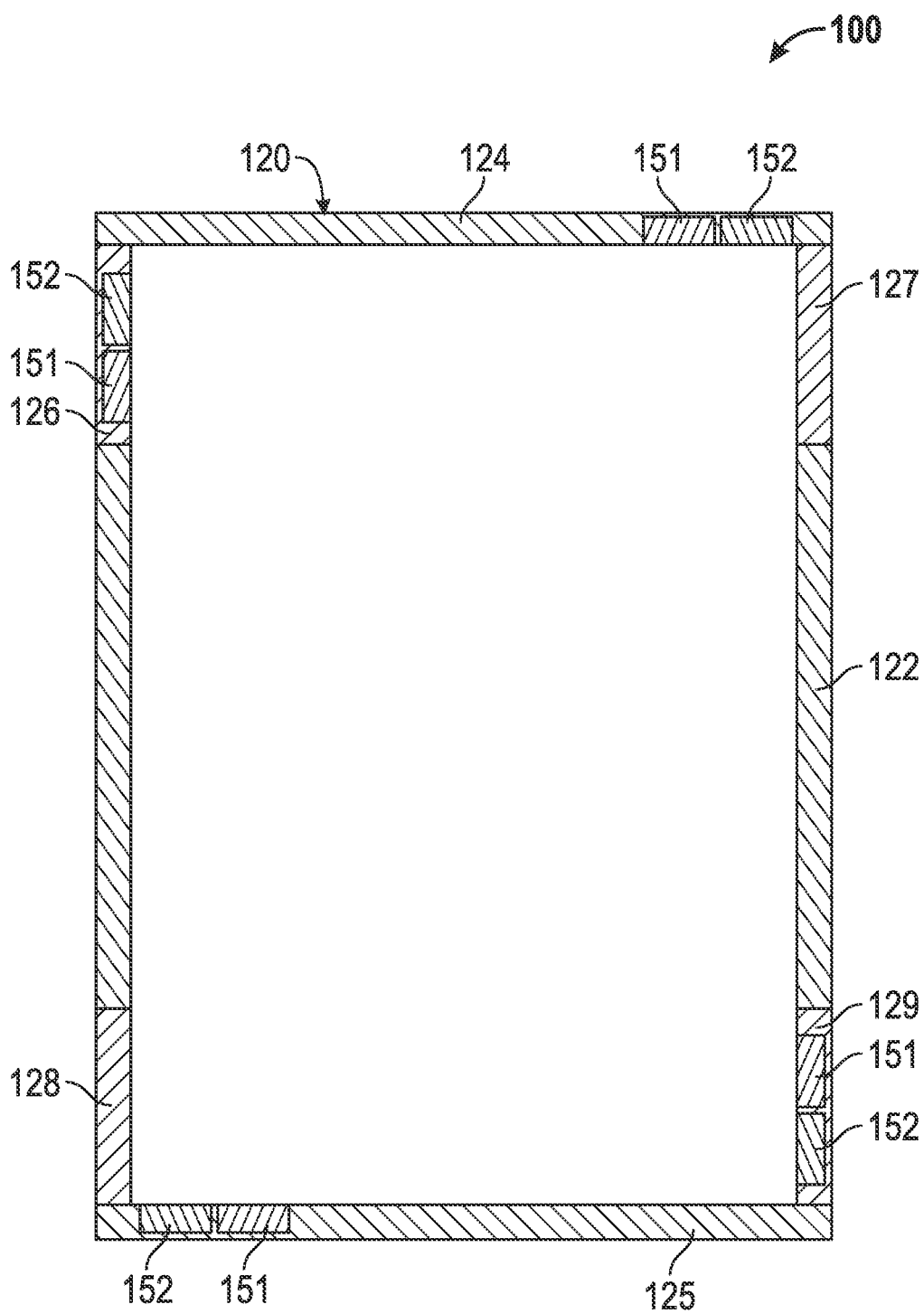


FIG. 2

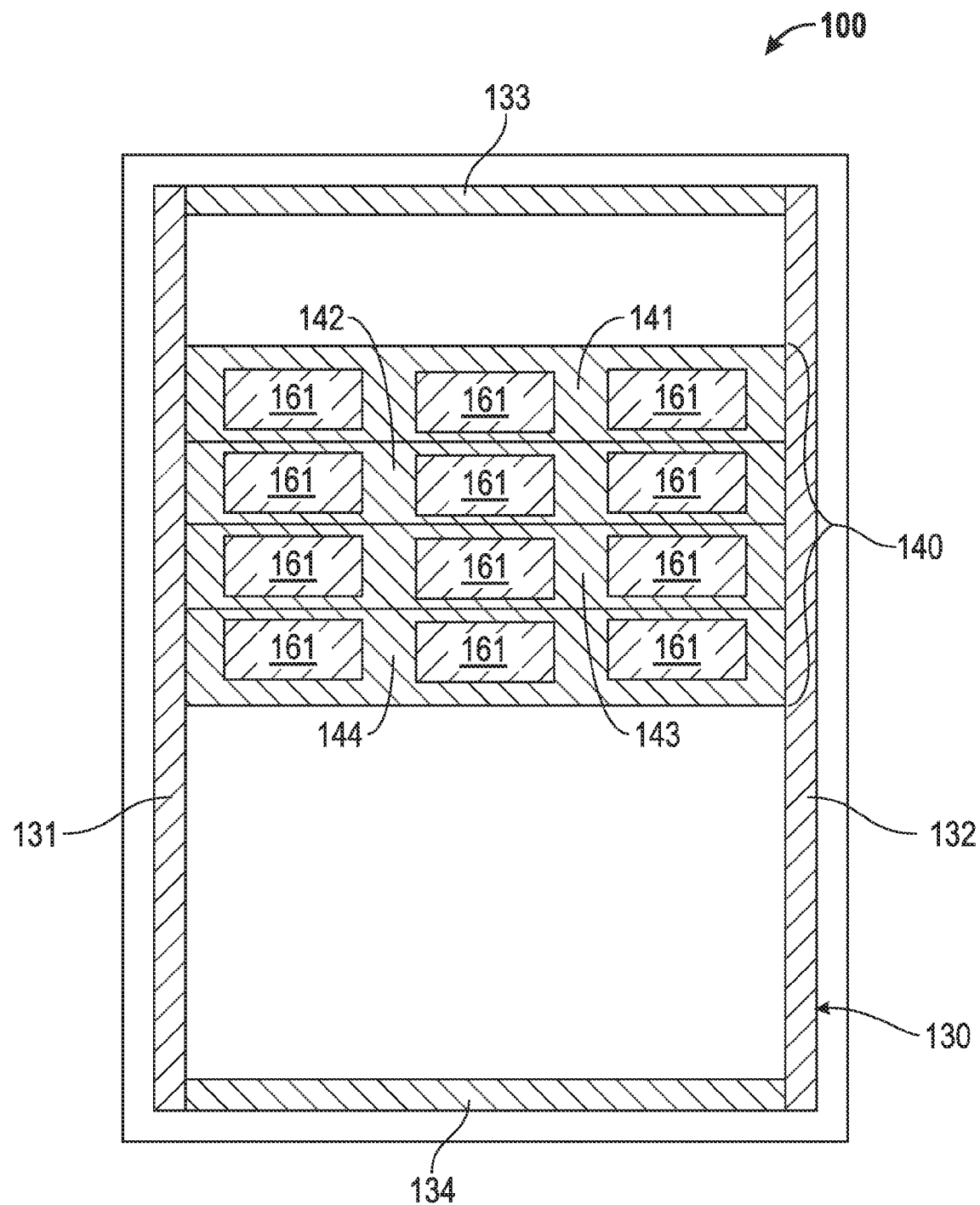


FIG. 3

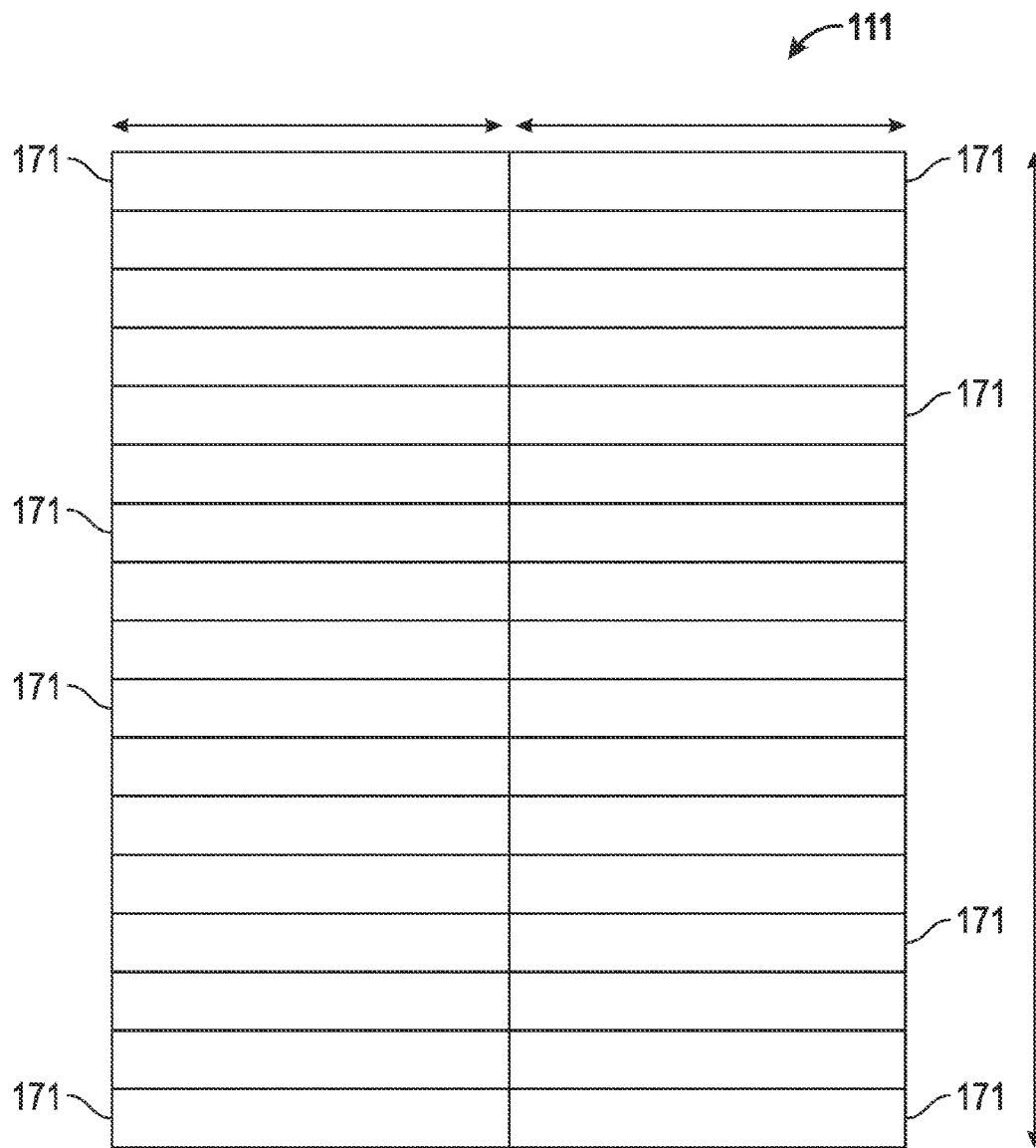


FIG. 4

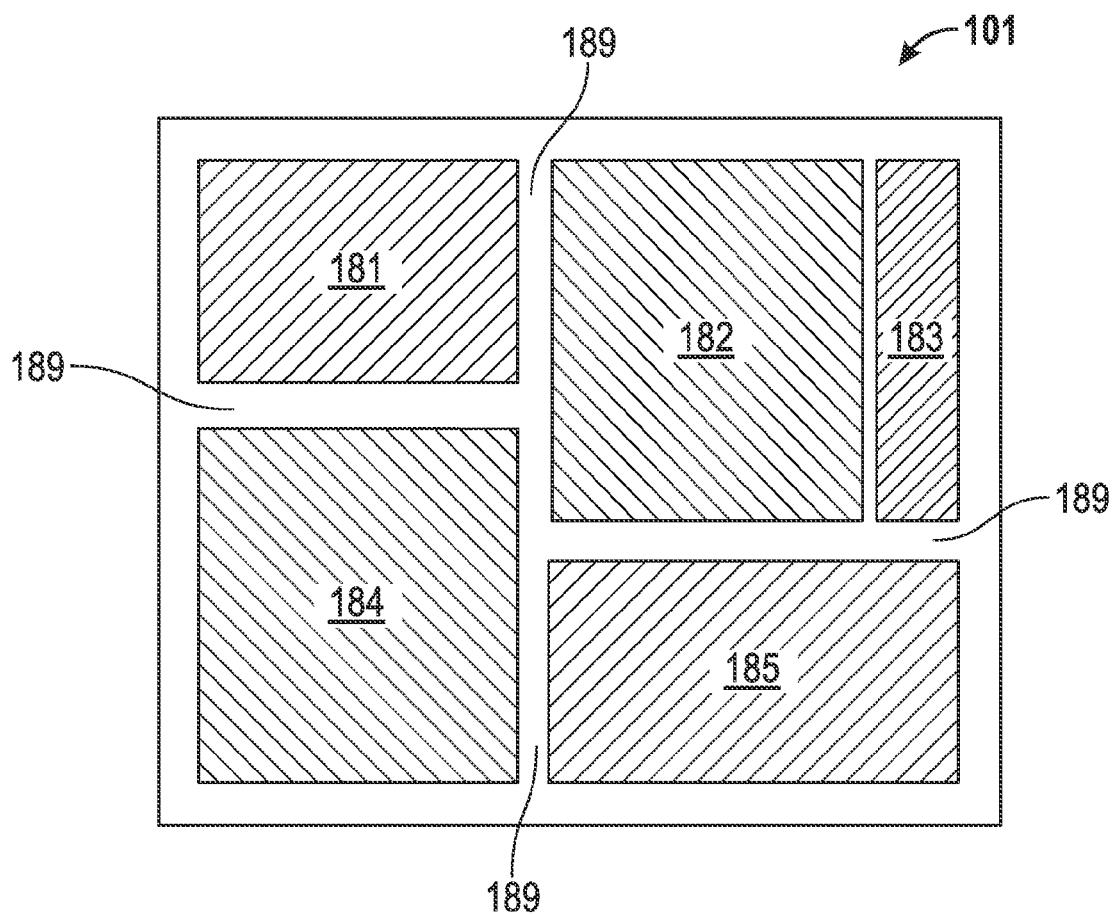


FIG. 5

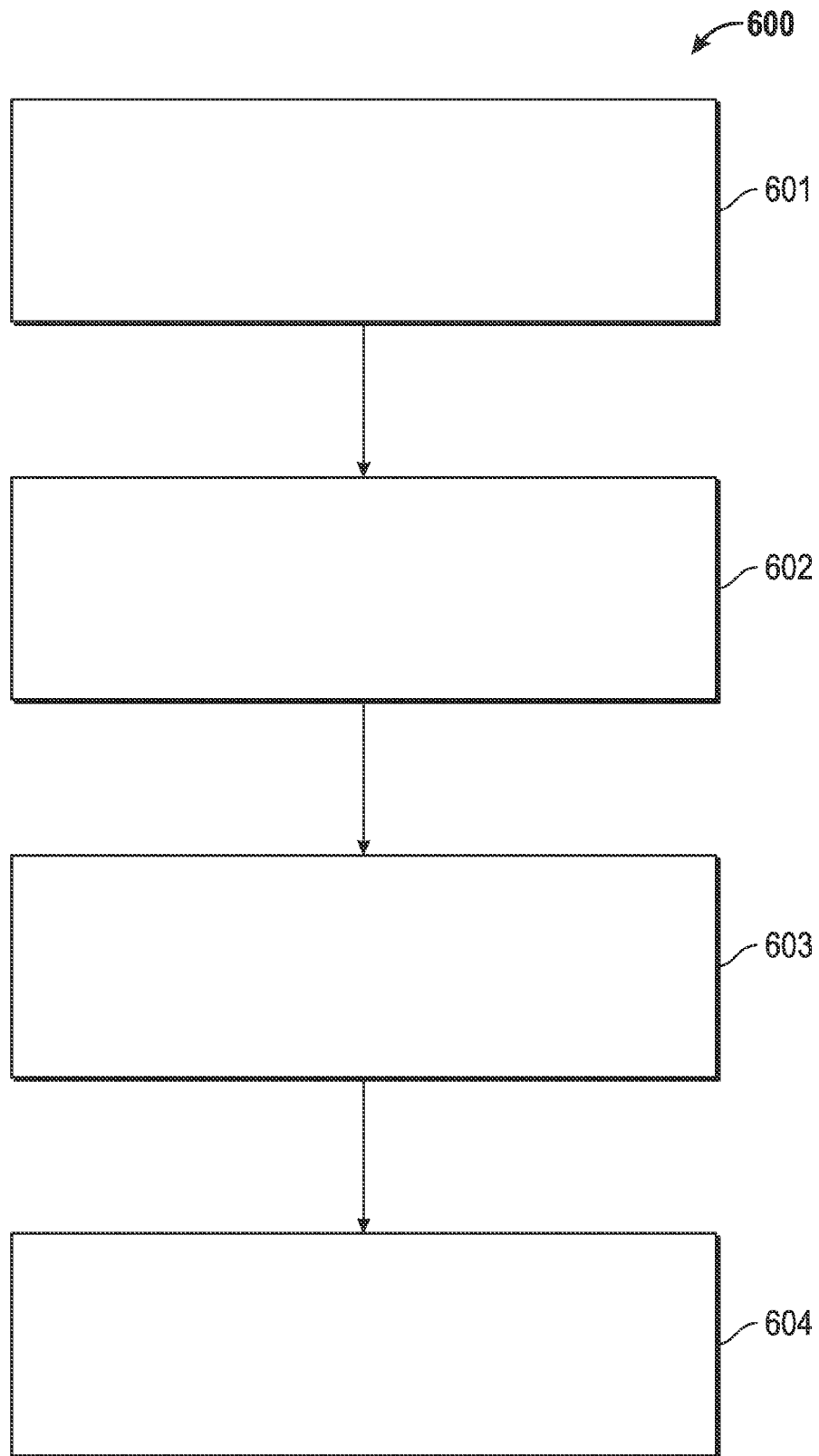


FIG. 6

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**SEMICONDUCTOR WAFERS EMPLOYING A  
FIXED-COORDINATE METROLOGY  
SCHEME AND METHODS FOR  
FABRICATING INTEGRATED CIRCUITS  
USING THE SAME**

**TECHNICAL FIELD**

The present disclosure generally relates to semiconductor wafers used in fabricating integrated circuits and methods for fabricating integrated circuits. More particularly, the present disclosure relates to a fixed-coordinate metrology scheme implemented on a semiconductor wafer and methods for fabricating integrated circuits using the same.

**BACKGROUND**

The majority of present day integrated circuits are implemented by using a plurality of interconnected field effect transistors (FETs), also called metal oxide semiconductor field effect transistors (MOSFETs), or simply MOS transistors. A MOS transistor includes a gate electrode as a control electrode and spaced apart source and drain regions between which a current can flow. A control voltage applied to the gate electrode controls the flow of current through a channel between the source and drain regions.

The production process leading to the provision of integrated circuits on a large scale typically includes a plurality of processing steps that take place on a thin wafer of semiconductor material, for example a monocrystalline silicon wafer. The wafer is subjected to a plurality of chemical and physical treatments and to photolithographic processes that lead to the definition of a complex three-dimensional topography constituting the integrated circuit architecture. A single wafer may contain hundreds of integrated circuits commonly called "chips" and arranged side by side, for example, and separated by scribing lines.

The term "metrology" broadly refers to the measurement and testing of objects. Metrology schemes are commonly used in the fabrication of integrated circuits. Metrology schemes are often used to measure features formed on the wafers to ensure that the features meet desired specifications, including the layout and spacing of the various integrated chips to be fabricated on the wafer. Various metrology methods may be used following any number of steps in a fabrication sequence to ensure that the semiconductor devices are formed within desired specifications.

In some fabrication processes, the first step in fabricating an integrated circuit (subsequent to the design of the integrated circuit) includes the design "tape-out" process, which begins with sending tape-out forms to the integrated circuit manufacturer. Tape-out forms are data files describing manufacturing related data and other details, such as mask tooling information for manufacturers or technology information. After tape-out forms are generated, descriptions of a circuit will be sent for manufacture. In current practice, metrology schemes for the semiconductor wafer are prepared based on the tape-out form. Thus, for each new tape-form that is received by the manufacturer, a new metrology scheme needs to be implemented specific to the respective wafer design. Currently, the preparation of a new metrology scheme for each tape-out form takes about a week's worth of time to complete, thus undesirably delaying the semiconductor fabrication process, and increasing fabrication expenses.

Accordingly, it is desirable to provide improved metrology schemes and improved methods for fabricating integrated circuits that reduce the time and expense involved in the

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design and implementation of metrology schemes. Additionally, it is desirable to provide a fixed-coordinate metrology scheme and methods for fabricating integrated circuits using a fixed-coordinate metrology scheme that does not need to be re-designed for each tape-out form. Furthermore, other desirable features and characteristics of the present disclosure will become apparent from the subsequent detailed description and the appended claims, taken in conjunction with the accompanying drawings and the foregoing technical field and background.

**BRIEF SUMMARY**

Semiconductor wafers employing a fixed coordinate metrology scheme and methods for fabricating integrated circuits using the same are disclosed. In an exemplary embodiment, a semiconductor wafer employed a fixed-coordinate metrology scheme includes an external scribe region in the form of a first rectangular ring, the first rectangular ring defining a first interior space inward from the external scribe region and an interior scribe region in the form of a second rectangular ring, disposed within the first interior space and immediately adjacent to the external scribe region at all points along its exterior perimeter, the second rectangular ring defining a second interior space inward from the interior scribe region, the second interior space being wholly within the first interior space. The semiconductor wafer further includes a technology-specific tile region disposed within the second interior space and immediately adjacent to the interior scribe region and an electrical testable scribe line measurement (ETSLM) region disposed within the second interior space and immediately adjacent to both the technology-specific tile region and the interior scribe region. Still further, the semiconductor wafer includes a free floorplan area disposed within the second interior space and immediately adjacent to both the ETSLM region and the interior scribe region.

In another exemplary embodiment, a method for fabricating an integrated circuit using a fixed-coordinate metrology scheme includes preparing a fixed-coordinate metrology scheme in accordance with a tape-out form and in integrated circuit layout design received by an integrated circuit manufacturer. The fixed coordinate metrology scheme includes an external scribe region in the form of a first rectangular ring, the first rectangular ring defining a first interior space inward from the external scribe region and an interior scribe region in the form of a second rectangular ring, disposed within the first interior space and immediately adjacent to the external scribe region at all points along its exterior perimeter, the second rectangular ring defining a second interior space inward from the interior scribe region, the second interior space being wholly within the first interior space. The fixed coordinate metrology scheme further includes a technology-specific tile region disposed within the second interior space and immediately adjacent to the interior scribe region and an electrical testable scribe line measurement (ETSLM) region disposed within the second interior space and immediately adjacent to both the technology-specific tile region and the interior scribe region. Still further, the fixed coordinate metrology scheme includes a free floorplan area disposed within the second interior space and immediately adjacent to both the ETSLM region and the interior scribe region. The method further includes providing metrology markings to a semiconductor wafer in accordance with the fixed-coordinate metrology scheme and the tape-out form, forming ETSLM structures within the ETSLM region and forming technology-specific tile-containing chips within the technology-specific tile

region, and fabricating a plurality of integrated circuit chips within the free floorplan area in accordance with the integrated circuit layout design.

#### BRIEF DESCRIPTION OF THE DRAWINGS

The present disclosure will hereinafter be described in conjunction with the following drawing figures, wherein like numerals denote like elements, and wherein:

FIG. 1 illustrates an exemplary fixed-coordinate metrology scheme in accordance with various embodiments of the present disclosure;

FIG. 2 illustrates the placement of certain metrology marks in the exemplary fixed-coordinate metrology scheme illustrated in FIG. 1;

FIG. 3 illustrates the placement of a scribe ring and electrical testable scribe line measurement (ETSLM) structures in the exemplary fixed-coordinate metrology scheme illustrated in FIG. 1;

FIG. 4 illustrates the placement of technology-specific tile structures in the exemplary fixed-coordinate metrology scheme illustrated in FIG. 1;

FIG. 5 illustrates the placement of integrated circuit chips in the exemplary fixed-coordinate metrology scheme illustrated in FIG. 1; and

FIG. 6 is a flowchart illustrating an exemplary method for fabricating an integrated circuit using a fixed-coordinate metrology scheme in accordance with various embodiments of the present disclosure.

#### DETAILED DESCRIPTION

The following detailed description is merely illustrative in nature and is not intended to limit the embodiments of the subject matter or the application and uses of such embodiments. Furthermore, there is no intention to be bound by any expressed or implied theory presented in the preceding technical field, background, brief summary, or the following detailed description.

The present disclosure provides improved methods for the fabrication of integrated circuits that include the use of a fixed-coordinate metrology scheme. As used herein, the adjective “fixed-coordinate” is used in reference to the fact the each individual region of the metrology scheme (as will be described below) is placed within the same physical location on the semiconductor wafer (with respect to the coordinate system of the wafer) regardless of the tape-out form that is being implemented by the metrology scheme. For the sake of brevity, conventional techniques related to integrated circuit device fabrication may not be described in detail herein. Moreover, the various tasks and process steps described herein may be incorporated into a more comprehensive procedure or process having additional steps or functionality not described in detail herein. In particular, various steps in the manufacture of semiconductor-based transistors are well-known and so, in the interest of brevity, many conventional steps will only be mentioned briefly herein or will be omitted entirely without providing the well-known process details.

The fixed-coordinate metrology schemes of the present disclosure may be implemented on a semiconductor wafer suitable for use in fabricating integrated circuits thereon. In some embodiments, the semiconductor wafer may be a silicon substrate having a (100) surface crystal orientation. The term “silicon substrate” is used herein to encompass the relatively pure silicon materials typically used in the semiconductor industry as well as silicon admixed with other elements such as germanium, carbon, and the like. A silicon

substrate may be a bulk silicon wafer, or it may be a thin layer of silicon on an insulating layer (commonly known as silicon-on-insulator or “SOI”) that, in turn, is supported by a carrier wafer. Alternatively, the semiconductor wafer can include alternative semiconductor materials such as germanium, gallium arsenide, or other semiconductor materials.

FIG. 1 illustrates an exemplary fixed-coordinate metrology scheme **100** in accordance with various embodiments of the present disclosure that may be implemented on a semiconductor wafer in the fabrication of integrated circuits. As noted in the Background of this disclosure, it is presently known in the art to prepare and design a metrology scheme based on each individual tape-out form that is received by the integrated circuit manufacturer from the integrated circuit designer. Such preparation and design may take up to a week to perform. The fixed-coordinate metrology scheme **100** shown in FIG. 1, and described in greater detail below, is provided to allow for its use with multiple different tape-out forms, thus reducing the time required to fabricate an integrated circuit once the design thereof and the tape-out forms are received at the integrated circuit manufacturer.

The various regions of the metrology scheme **100**, which are to be provided at the same location on the semiconductor wafer (with respect to the coordinate system thereof) regardless of the tape-out form being implemented will be briefly introduced in connection with the description of FIG. 1. Thereafter, the individual regions will be described in greater detail in connection with the description of FIGS. 2-5. As shown in FIG. 1, the fixed-coordinate metrology scheme **100** may include a “free floorplan area” **101**. The free floorplan area **101** does not include any metrology markings, and is the area of the semiconductor wafer in which the various integrated circuit “chips” are to be fabricated, with scribe lines separating the various chips from one another. The free floorplan area is described in greater detail below with regard to FIG. 5.

The fixed-coordinate metrology scheme **100** may further include a technology-specific tile region **110**. As will be appreciated, a semiconductor wafer may include integrated circuit chips (in free floorplan area **101**) having different integrated circuit technologies, such as super low power (SLP), super high performance (SHP), high performance plus (HPP), low power high performance (LPH), and others as are known in the art. Thus, technology-specific tile region **110** may include a plurality of technology-specific tile-containing chips **111-113**, which may be separated by separation (or blank) regions **118**, **119**. Each tile-containing chip **111-113** includes a plurality of technology-specific tiles, as will be discussed in greater detail below with regard to FIG. 4. These tiles include instructions and other information necessary in the fabrication of integrated circuits in accordance with the specific technology. Separation regions **118**, **119** do not include any technology-specific tiles or other metrology markings, and are included in the metrology scheme to provide separation between the tile-containing chips **111-113**. Further, although three tile-containing chips **111-113** are shown in the scheme of FIG. 1, separated by two separation regions **118**, **119**, it will be appreciated that more or fewer tile-containing chips may be provided in tile region **110**, separated by a correspond number of separation regions.

With continued reference to FIG. 1, the fixed-coordinate metrology scheme **100** may further include an external scribe region **120**. External scribe region **120** includes a plurality of scribe marking areas **124-129** and a plurality of machine vision system (MVS) target areas **121**, **122**. External scribe region **120** may generally occupy an outer-most “ring” of the fixed-coordinate metrology scheme **100**. Scribe marking

areas **124-129** are provided as regions in which a plurality of tape-out form-specific metrology markings may be provided, such as overlay markings and critical dimension (CD) markings (or other metrology markings), as will be discussed in greater detail below with regard to FIG. 2. MVS target areas **121, 122** are provided as regions in which alignment markings may be provided for particular lithography tools. For example, the term MVS refers to the alignment markings used with the Ultratech Lithography Tool available from Ultratech of San Jose, Calif., USA. Of course, if other tools are used, other markings may be provided in target areas **121, 122**.

Additionally, the fixed-coordinate metrology scheme **100** may include an interior scribe region **130**, positioned immediately adjacent to and within the external scribe region **120**, and which defines a width of an electrical testable scribe line measurement (ETSLM) region **140**. Scribe region **130** includes wafer alignment markings and other metrology markings, and is configured to provide spacing between the external scribe region **120**, which include metrology markings, and a plurality of interior features of the metrology scheme **100**, such as the free floorplan area **101** (including the integrated circuit chips), the technology-specific tile region **110** (including the technology-specific tile-containing chips **111-113**), and the ETSLM region **140**. Scribe region **130** includes at least two vertical frame elements **131, 132** and at least two horizontal frame elements **133, 134**. Each of the frame elements **131-134** may include wafer alignment marking and/or other metrology markings, as dictated by the specific tape-out form provided. With regard to the ETSLM region **140**, this region may include a plurality of horizontally-oriented ETSLM scribe regions **141-144**, each of which may contain one or more ETSLM structures including, for example, probe check macros, FET macros, resistance macros, or other ETSLM structures as may be required for the specific tape-out form provided. As known in the art, probe check macros may be provided to determine whether there are any ET program errors, FET macros may be provided to predict chip performance, and resistance macros may be provided to test back-end-of line (BEOL) processes, for example the resistance of various metal wires deposited during BEOL processes. Of course, other macros as necessary and known in the art for a particular design may be provided in the scribe regions **141-144**. Greater detail with regard to the interior scribe region **130** and the ETSLM region **140** is provided below in the description accompanying FIG. 3.

Reference is now made to FIG. 2, which as noted above, illustrates in greater detail the external scribe region **120**. While the area within region **120** is blank, it will be appreciated that this is done for ease of illustration and to place emphasis on the details of region **120**; no difference in overall structure in comparison to the fixed-coordinate metrology scheme presented initially in FIG. 1 is intended. As shown in FIG. 2, the external scribe region **120** includes a plurality of scribe marking areas **124-129**. At least two of the scribe marking areas **124, 125** may be horizontally oriented areas that define upper and lower portions of the region **120**, which as noted above may be configured as a rectangular "ring." At least two MVS target areas **121, 122** may be vertically oriented and may be placed within side portions of the region **120**. A plurality (for example four) vertically oriented scribe marking areas **126-129** may be provided to separate the MVS target areas **121, 122** from the horizontally oriented scribe marking areas **124, 125**. For example, as shown in FIG. 2, a vertically oriented scribe marking area may be placed both above and below each of the MVS target areas **121, 122**. Generally, any of the plurality of scribe marking areas **124-**

**129** may include both CD metrology markings **151** and overlay metrology markings **152**. However, not all of areas **124-129** need include either of such markings **151, 152**. The placement of the markings **151, 152** will generally depend of the tape-out form provided. MVS target area **121** may be the MVS target, as described above, and may have dimensions, for example, of about 2044 microns in height and about 44 microns in width, and area **122** may be a chrome blank area, provided to avoid double printing by blocking all light from passing through a reticle. The height (vertical dimension) and length (horizontal dimension) of the scribe region **120** "ring" is dependent upon the particular semiconductor wafer size at issue, and varies across technology nodes. The width of each of the portions **121-129** (measured from the exterior of the ring to the interior of the ring) may be substantially equal, and may be from about 0.5 mm to about 3 mm, again depending on the particular semiconductor wafer size at issue. Thus, the external scribe region **120** may be placed in fixed coordinates with respect to the semiconductor wafer, while providing the flexibility to accommodate various different metrology marking schemes and MVS target schemes according to various different tape-out forms as may be received by the semiconductor manufacturer.

Reference is now made to FIG. 3, which as noted above illustrates in greater detail the interior scribe region **130** and the ETSLM region **140**. While the area within region **130** is blank (excepting the ETSLM region **140**), it will be appreciated that this is done for ease of illustration and to place emphasis on the details of regions **130** and **140**; no difference in overall structure in comparison to the fixed-coordinate metrology scheme presented initially in FIG. 1 is intended. The interior scribe region is formed of at least two vertical frame elements **131, 132**, positioned adjacent to and within the MVS target areas **121, 122** and the vertically oriented scribe marking areas **126-129**, and at least two horizontal frame elements **133, 134**, positioned adjacent to and within the horizontally oriented scribe marking areas **124, 125**. Thus, interior scribe region **130** defines a rectangular "ring," concentrically within and adjacent to the region **120**. The height (vertical dimension) and length (horizontal dimension) of the interior scribe region **130** "ring" is dependent upon the particular semiconductor wafer size at issue. The width of each of the frame elements **131-134** (measured from the exterior of the ring to the interior of the ring) may be substantially equal, and may be from about 0.5 mm to about 3 mm, again depending on the particular semiconductor wafer size at issue. Each of the frame elements **131-134** may include wafer alignment marking and/or other metrology markings (not separately illustrated), as dictated by the specific tape-out form provided. The content and placement of such markings will generally depend of the tape-out form provided. Thus, the interior scribe region **130** may be placed in fixed coordinates with respect to the semiconductor wafer, while providing the flexibility to accommodate various different metrology marking schemes according to various different tape-out forms as may be received by the semiconductor manufacturer.

With continued reference to FIG. 3, the ETSLM region **140** includes a plurality of horizontally-oriented ETSLM scribe regions **141-144**, each of which may contain one or more ETSLM structures **161**. Region **140** is provided between and adjacent to frame elements **131, 132**, and immediately below and adjacent to technology-specific tile region **110** (which, as noted above, is provided immediately below and adjacent to frame element **133**). Each of the structures **161** may include probe check macros, FETs, resistance macros, etc., as described above. Each region **141-144** may include one, two,

three, or more ETSLM structures **161**. The number of scribe regions **141-144** is provided may be dependent upon the particular tape-out form provided (for example, one, two, three, four, or more). The length (horizontal dimension) of the scribe region **120** “ring” is dependent upon the particular semiconductor wafer size at issue. The width of each of the portions regions **141-144** (measured in the same manner as the width of frame elements **133, 134**) may be substantially equal, and may be from about 0.5 mm to about 3 mm, again depending on the particular semiconductor wafer size or technology node(s) at issue. Structures **161** may generally have lengths and widths that are less than the length and width of the regions **141-144**, so as to fit within the bounds of regions **141-144**.

With reference now to FIG. 4, as noted above, greater detail is provided regarding the technology-specific tile-containing chips **111-113** (an exemplary chip **111** is shown in FIG. 4). The illustrated technology-specific tile-containing chip **111** includes a plurality of technology-specific tiles **171**, each of which may include instructions and other information necessary in the fabrication of integrated circuits (in free floorplan area **101**) in accordance with the specific technologies of such integrated circuits, for example SLP, SHP, HPP, LPH, and others as are known in the art. A chip **111** may include one or more columns of tiles **171** (two are shown in FIG. 4), and one or more rows of tiles **171** (seventeen are shown in FIG. 4). The number of tile **171** provided is generally dependent on the specific technology and on the tape-out form provided, and may vary from embodiment to embodiment. The configuration of the chip **111** is generally square, and may have side lengths from about 3 mm to about 5 mm, for example about 4 mm, depending on the semiconductor wafer size. The tiles **171** may have a length of about 2 mm, and a height that is dependent upon the number of tiles required for a given technology. Thus, each of the tiles **111-113** may be placed in fixed coordinates with respect to the semiconductor wafer, while providing the flexibility to accommodate various numbers and configurations of tiles **171** according to various different technologies and tape-out forms as may be received by the semiconductor manufacturer.

Further, with reference now to FIG. 5, greater detail is provided in connection with the free floorplan area **101**. Free floor plan area **101** is provided between and adjacent to frame elements **131, 132**, and immediately below and adjacent to ETSLM region **140**. Free floorplan area **101** is also provided immediately above and adjacent to frame element **134**. Generally speaking, free floorplan area **101** can include any number of integrated circuit chips **181-185**, with scribe lines **189** being provided in between chips **181-185**, and bordering the external boundaries of area **101**. Various sizes and configurations of chips **181-185** may be included, as shown in FIG. 5. The overall size of free floorplan area **101** is dependent upon the size of the semiconductor wafer, and may vary from embodiment to embodiment. Thus, the free floorplan area **101** may be placed in fixed coordinates with respect to the semiconductor wafer, while providing the flexibility to accommodate various numbers and configurations of integrated circuit chips **181-185** according to various different technologies and tape-out forms as may be received by the semiconductor manufacturer.

With the metrology scheme being configured with respect to the tape-out form and integrated circuit layout design received by the manufacturer, but within the fixed-coordinate metrology scheme described above, fabrication of the integrated circuit may commence in accordance with method **600** illustrated in the flowchart shown in FIG. 6. Method **600** includes a step **601** of preparing a fixed-coordinate metrology

scheme in accordance with a tape-out form and in integrated circuit layout design received by the integrated circuit manufacturer. Step **601** is carried out in accordance with the principles described above regarding the fixed-coordinate metrology scheme **100**, for example. Method **600** continues with step **602** of providing metrology markings to the semiconductor wafer in accordance with the fixed-coordinate metrology scheme **100**. These markings may include, for example, any of the CD or overlay markings **151, 152** included within the external scribe region **120**, or the wafer alignment and other metrology markings included within the interior scribe region **130**. Method **600** also includes a step of forming the ETSLM structures **161** and the technology-specific tile-containing chips **111-113** on the semiconductor wafer in accordance with the tape-out form and the integrated circuit layout design, and also within the fixed-coordinate metrology scheme **100** (i.e., within regions **140** and **110**, respectively). Further, method **600** includes a step **604** of fabricating the integrated circuit chips **181-185** within free floorplan area **101** in accordance with the integrated circuit layout design. Fabrication of the integrated circuit chips **181-185** may be performed using processing steps that as are well-known in the art (not illustrated). These steps conventionally include, for example, preparing photolithographic masks and using the masks to pattern a plurality of features on the semiconductor wafer using material deposition and etching procedures, for example, the formation of semiconductive structures, the formation of metals gates, forming various insulating layers, the formation of doped source and drain regions, the formation of contacts (formed by depositing a photoresist material layer over the insulating layer, lithographic patterning, etching to form contact voids, and depositing a conductive material in the voids to form the contacts), and the formation of one or more patterned conductive layers, among many others. The subject matter disclosed herein is not intended to exclude any subsequent processing steps to form and test the completed integrated circuits within free floorplan area **101** as are known in the art.

Accordingly, embodiments of the present disclosure provide a fixed-coordinate metrology scheme suitable for use in the fabrication of integrated circuits. The fixed coordinate-metrology scheme includes various regions that are placed in fixed coordinates with respect to the semiconductor wafer on which the integrated circuit is to be manufactured. Various metrology markings, ETSLM structures, technology-specific chips, and of course the integrated circuits themselves are placed within the fixed-coordinate regions according to the specific tape-out form and integrated circuit layout design being implemented. In this manner, it is possible to avoid the need to redesign and reconfigure a metrology scheme for each tape-out form received, thus saving significant fabrication time and expense.

While at least one exemplary embodiment has been presented in the foregoing detailed description, it should be appreciated that a vast number of variations exist. It should also be appreciated that the exemplary embodiment or exemplary embodiments are only examples, and are not intended to limit the scope, applicability, or configuration of the invention in any way. Rather, the foregoing detailed description will provide those skilled in the art with a convenient road map for implementing the exemplary embodiment or exemplary embodiments. It should be understood that various changes can be made in the function and arrangement of elements without departing from the scope of the invention as set forth in the appended claims and the legal equivalents thereof.

What is claimed is:

1. A semiconductor wafer employing a fixed-coordinate metrology comprising:

an external scribe region in the form of a first rectangular ring, the first rectangular ring defining a first interior space inward from the external scribe region, wherein the external scribe region comprises a plurality of overlay markings and/or critical dimension (CD) markings, and wherein the external scribe region comprises, as the first rectangular ring, two horizontal scribe marking areas defining upper and lower portions of the external scribe region and two MVS target areas disposed along opposite side regions of the external scribe region, each MVS target area being separated from the two horizontal scribe marking areas by two vertical scribe marking areas;

an interior scribe region in the form of a second rectangular ring, disposed within the first interior space and immediately adjacent to the external scribe region at all points along its exterior perimeter, the second rectangular ring defining a second interior space inward from the interior scribe region, the second interior space being wholly within the first interior space;

a technology-specific tile region disposed within the second interior space and immediately adjacent to the interior scribe region;

an electrical testable scribe line measurement (ETSLM) region disposed within the second interior space and immediately adjacent to both the technology-specific tile region and the interior scribe region; and

a free floorplan area disposed within the second interior space and immediately adjacent to both the ETSLM region and the interior scribe region.

2. The semiconductor wafer of claim 1, wherein the horizontal and the vertical scribe marking areas comprise the overlay markings and/or CD markings, and wherein the MVS target areas comprise alignment markings for a specific lithography tool to be employed.

3. The semiconductor wafer of claim 1, wherein the interior scribe region comprises a plurality of wafer alignment markings.

4. The semiconductor wafer of claim 3, wherein the interior scribe region comprises at least two vertical frame elements and at least two horizontal frame elements to form the second rectangular ring.

5. The semiconductor wafer of claim 1, where the technology-specific tile region comprises a plurality of technology-specific tile-containing chips, each chip of the plurality of chips being separated from one another by a separation region.

6. The semiconductor wafer of claim 5, wherein each chip of the plurality of chips comprises a plurality of technology specific tiles, each technology specific tile comprising instructions regarding the fabrication of an integrated circuit according to a specific technology.

7. The semiconductor wafer of claim 6, wherein the specific technology is selected from the group consisting of: super low power (SLP), super high performance (SHP), high performance plus (HPP), low power high performance (LPH).

8. The semiconductor wafer of claim 1, wherein the ETSLM region comprises a plurality of ETSLM structures selected from the group consisting of: probe check macros, FETs, and resistance macros.

9. The semiconductor wafer of claim 8, wherein the ETSLM region comprises a plurality of horizontal frame elements, wherein the horizontal frame elements comprise the ETSLM structures.

10. The semiconductor wafer of claim 1, wherein the free floorplan area comprises a plurality of integrated circuit chips separated by scribe lines.

11. The semiconductor wafer of claim 10, wherein the free floorplan area is free of metrology markings.

12. A method for fabricating an integrated circuit comprising:

preparing a fixed-coordinate metrology scheme in accordance with a tape-out form and in integrated circuit layout design received by an integrated circuit manufacturer, wherein the fixed coordinate metrology scheme comprises:

an external scribe region in the form of a first rectangular ring, the first rectangular ring defining a first interior space inward from the external scribe region, wherein the external scribe region comprises a plurality of overlay markings and/or critical dimension (CD) markings, and wherein the external scribe region comprises, as the first rectangular ring, two horizontal scribe marking areas defining upper and lower portions of the external scribe region and two MVS target areas disposed along opposite side regions of the external scribe region, each MVS target area being separated from the two horizontal scribe marking areas by two vertical scribe marking areas;

an interior scribe region in the form of a second rectangular ring, disposed within the first interior space and immediately adjacent to the external scribe region at all points along its exterior perimeter, the second rectangular ring defining a second interior space inward from the interior scribe region, the second interior space being wholly within the first interior space;

a technology-specific tile region disposed within the second interior space and immediately adjacent to the interior scribe region;

an electrical testable scribe line measurement (ETSLM) region disposed within the second interior space and immediately adjacent to both the technology-specific tile region and the interior scribe region; and

a free floorplan area disposed within the second interior space and immediately adjacent to both the ETSLM region and the interior scribe region;

providing metrology markings to a semiconductor wafer in accordance with the fixed-coordinate metrology scheme and the tape-out form;

forming ETSLM structures within the ETSLM region and forming technology-specific tile-containing chips within the technology-specific tile region; and

fabricating a plurality of integrated circuit chips within the free floorplan area in accordance with the integrated circuit layout design.

13. The method of claim 12, wherein providing metrology markings comprises providing metrology markings within the interior scribe region.

14. The method of claim 13, wherein providing metrology markings comprises providing wafer alignment markings within the interior scribe region.

15. The method of claim 14, wherein metrology markings are not provided within the free floorplan area.

16. The method of claim 12, wherein fabricating the plurality of integrated circuit chips comprises employing one or more of a masking, patterning, etching, or deposition procedure.

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**17.** The method of claim **12**, further comprising providing the semiconductor wafer.

\* \* \* \* \*

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